



75NM65-U3

Preliminary

Power MOSFET

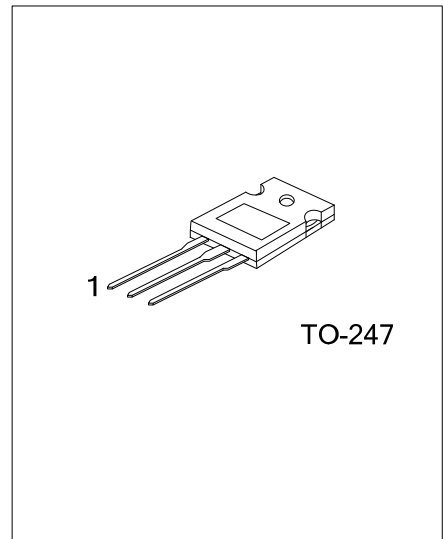
75A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

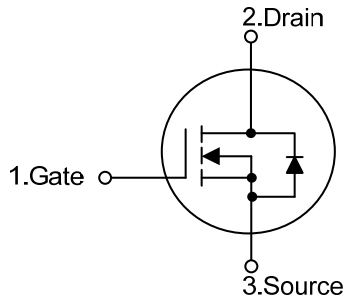
The **UTC 75NM65-U3** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 50 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=30\text{A}$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness



SYMBOL



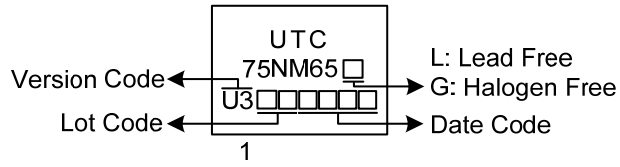
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
75NM65L-U3-T47-T	75NM65G-U3-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

75NM65G-U3-T47-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) T47: TO-247
	(3)Version Code	(3) Version U3
	(4)Green Package	(4) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	650	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	Continuous	I_D	75
	Pulsed (Note 2)	I_{DM}	165
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	1600
Peak Diode Recovery dv/dt (Note 4)	dv/dt	8.5	V/ns
Power Dissipation	P_D	240	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 5.7\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 30\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	40	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	0.52	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

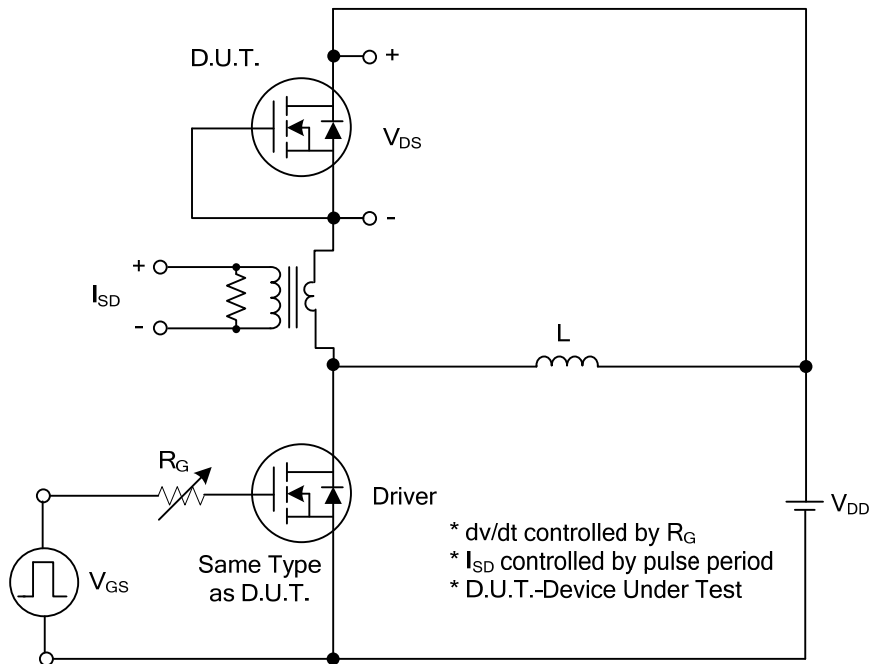
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A			50	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1MHz		4497		pF
Output Capacitance	C _{OSS}			1869		pF
Reverse Transfer Capacitance	C _{RSS}			133		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =520V, V _{GS} =10V, I _D =75A (Note 1, 2)		204		nC
Gate-Source Charge	Q _{GS}			29		nC
Gate-Drain Charge	Q _{DD}			125		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =75A, R _G =25Ω (Note 1, 2)		75		ns
Turn-On Rise Time	t _R			81		ns
Turn-Off Delay Time	t _{D(OFF)}			257		ns
Turn-Off Fall Time	t _F			92		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I _S				75	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				165	A
Drain-Source Diode Forward Voltage	V _{SD}	I _S =60A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _S =30A, V _{GS} =0V, dI _F /dt=100A/μs		656		ns
Body Diode Reverse Recovery Charge	Q _{rr}				14.5	

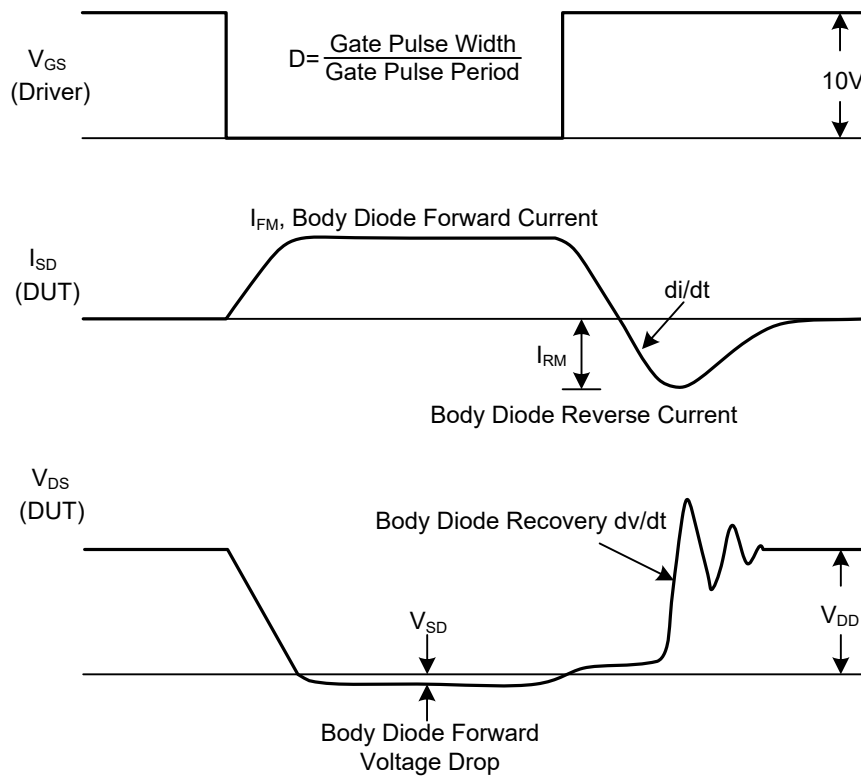
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

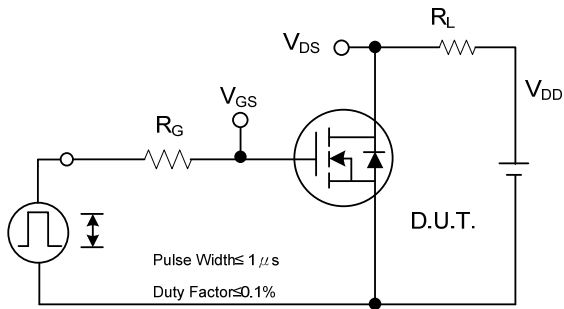


Peak Diode Recovery dv/dt Test Circuit

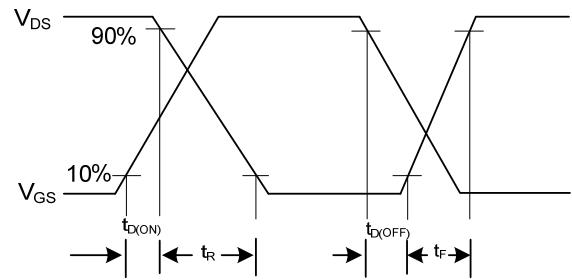


Peak Diode Recovery dv/dt Waveforms

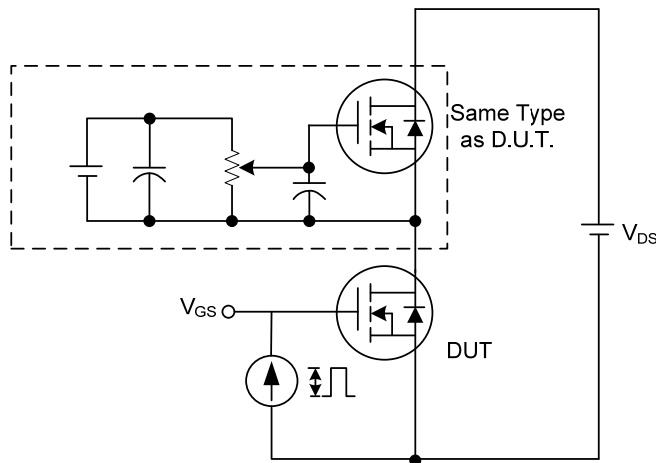
■ TEST CIRCUITS AND WAVEFORMS



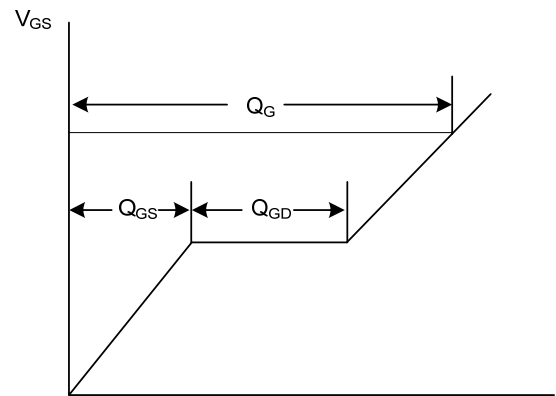
Switching Test Circuit



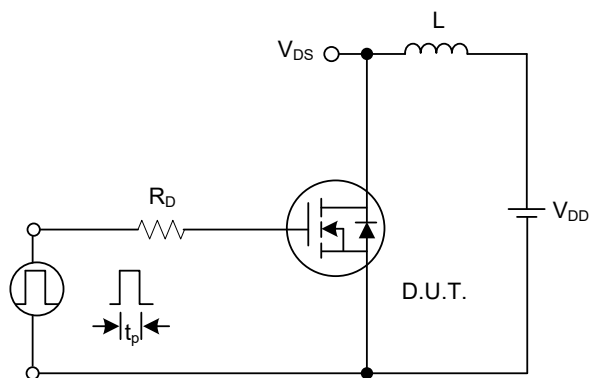
Switching Waveforms



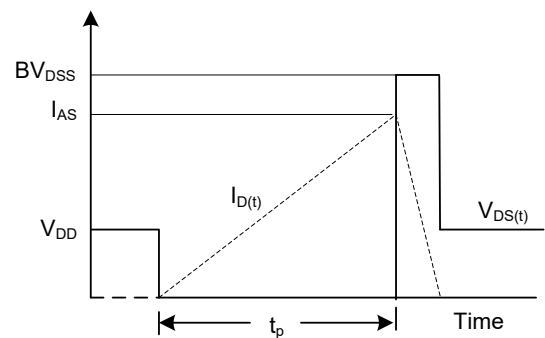
Gate Charge Test Circuit



Charge
Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.